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Electron-mediated ferromagnetism and negative s - d exchange splitting in semiconductors<sup>1</sup> SU-HUAI WEI, GUSTAVO M. DALPIAN, National Renewable Energy Laboratory — Magnetic semiconductors have many unique physical properties that can be used for magneto-optical and spintronic applications. Currently, most of the studies on magnetic semiconductors are focused on hole-mediated FM systems. In this work we discuss several approaches that can enhance the spin- splitting at the conduction band edge and consequently induce electron-mediated stabilization of ferromagnetic semiconductors. We show that kinetic s - d coupling can be introduced through chemical ordering and/or strain. We find that quantum confinement has a large effect on the spin- splitting at the conduction band edge. It can effectively reverse the sign of the conduction band splitting, thus, sheding light on the recent puzzling experimental observation that s - d exchange splitting is negative in semiconductor superlattices. Finally, we show that, using rare-earth elements as magnetic dopants, the symmetry-allowed s - fcoupling can lead to a large splitting at the conduction band edge.

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